

# A fast, high-endurance and scalable non-volatile memory Ta<sub>2</sub>O<sub>5</sub><sup>x</sup>/TaO<sub>2</sub><sup>x</sup> bilayer structures

Nature Materials

10, 625-630

DOI: 10.1038/nmat3070

Citation Report

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5	Enhanced and reproducible X-ray emission in a low-energy plasma focus. Europhysics Letters, 2006, 73, 42-48.	2.0	18
6	Filamentary-switching model in RRAM for time, energy and scaling projections. , 2011, , .		39
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25	Resistive switching and activity-dependent modifications in Ni-doped graphene oxide thin films. Applied Physics Letters, 2012, 101, 063104.	3.3	33
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